

### PDFN56



Pin Definition:1. Source8. Drain2. Source7. Drain3. Source6. Drain4. Gate5. Drain

### **Key Parameter Performance**

| Parameter                 | Value | Unit |
|---------------------------|-------|------|
| V <sub>DS</sub>           | 100   | V    |
| R <sub>DS(on)</sub> (max) | 12    | mΩ   |
| Qg                        | 145   | nC   |

#### **Block Diagram**

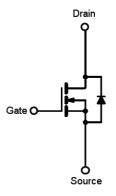
Features

- Low On-Resistance
- Low Input Capacitance
- Low Gate Charge

#### **Ordering Information**

| Part No.          | Package | Packing            |  |  |  |
|-------------------|---------|--------------------|--|--|--|
| TSM120N10PQ56 RLG | PDFN56  | 2.5kpcs / 13" Reel |  |  |  |

**Note:** "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



N-Channel MOSFET

#### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

| Parameter                             |                      | Symbol           | Limit       | Unit |  |
|---------------------------------------|----------------------|------------------|-------------|------|--|
| Drain-Source Voltage                  |                      | V <sub>DS</sub>  | 100         | V    |  |
| Gate-Source Voltage                   |                      | V <sub>GS</sub>  | ±20         | V    |  |
| Continuous Drain Current (Note 3)     | T <sub>C</sub> =25°C |                  | 58          | А    |  |
|                                       | T <sub>A</sub> =25°C | - I <sub>D</sub> | 16.1        |      |  |
| Drain Current-Pulsed (Note 1)         |                      | I <sub>DM</sub>  | 150         | А    |  |
| Single Pulse Avalanche Energy L=0.5mH |                      | E <sub>AS</sub>  | 156         | mJ   |  |
| Maximum Power Dissipation (Note 2)    | T <sub>C</sub> =25°C |                  | 36          | W    |  |
|                                       | T <sub>A</sub> =25°C | – P <sub>D</sub> | 2           |      |  |
| Storage Temperature Range             |                      | T <sub>STG</sub> | -55 to +150 | °C   |  |
| Operating Junction Temperature Range  |                      | TJ               | -55 to +150 | °C   |  |

#### **Thermal Performance**

| Parameter                                | Symbol           | Limit | Unit |
|--|------------------|-------|------|
| Thermal Resistance - Junction to Case    | R <sub>eJC</sub> | 1.2   | °C/W |
| Thermal Resistance - Junction to Ambient | $R_{\Theta JA}$  | 62    | °C/W |



#### Electrical Specifications (T<sub>J</sub>=25°C unless otherwise noted)

| Parameter                             | Conditions                                 | Symbol              | Min | Тур  | Max  | Unit |
|---------------------------------------|--|---------------------|-----|------|------|------|
| Static                                |  |                     |     | •    |      |      |
| Drain-Source Breakdown Voltage        | $V_{GS} = 0V, I_D = 250\mu A$              | BV <sub>DSS</sub>   | 100 |      |      | V    |
| Drain-Source On-State Resistance      | $V_{GS} = 10V, I_D = 30A$                  | R <sub>DS(ON)</sub> |     | 10   | 12   | mΩ   |
| Gate Threshold Voltage                | $V_{DS} = V_{GS}, I_D = 250 \mu A$         | V <sub>GS(TH)</sub> | 2   | 3    | 4    | V    |
| Zero Gate Voltage Drain Current       | $V_{DS} = 80V, V_{GS} = 0V$                | I <sub>DSS</sub>    |     |      | 1    | μA   |
| Gate Body Leakage                     | $V_{GS} = \pm 20V, V_{DS} = 0V$            | I <sub>GSS</sub>    |     |      | ±100 | nA   |
| Dynamic                               |  |                     |     |      | •    |      |
| Total Gate Charge                     | $V_{DS} = 50V, I_D = 30A,$                 | Qg                  |     | 145  |      | nC   |
| Gate-Source Charge                    |  | Q <sub>gs</sub>     |     | 25   |      |      |
| Gate-Drain Charge                     | V <sub>GS</sub> = 10V                      | $Q_{gd}$            |     | 43   |      |      |
| Input Capacitance                     | $V_{DS} = 30V, V_{GS} = 0V,$<br>f = 1.0MHz | C <sub>iss</sub>    |     | 3902 |      |      |
| Output Capacitance                    |  | C <sub>oss</sub>    |     | 251  |      | pF   |
| Reverse Transfer Capacitance          |  | C <sub>rss</sub>    |     | 93   |      | 1    |
| Switching                             |  |                     |     |      | •    |      |
| Turn-On Delay Time                    |  | t <sub>d(on)</sub>  |     | 27   |      |      |
| Turn-On Rise Time                     | $V_{GS} = 10V, V_{DS} = 50V,$              | t <sub>r</sub>      |     | 13   |      |      |
| Turn-Off Delay Time                   | $R_{\rm G} = 3\Omega, I_{\rm D} = 30A$     | t <sub>d(off)</sub> |     | 15   |      | ns   |
| Turn-Off Fall Time                    |  | t <sub>f</sub>      |     | 42   |      |      |
| Drain-Source Diode Characteristic     | s and Maximum Rating                       | •                   |     | •    |      |      |
| Drain-Source Diode Forward<br>Voltage | V <sub>GS</sub> =0V, I <sub>S</sub> =30A   | $V_{SD}$            |     |      | 1.3  | V    |
| Reverse Recovery Time                 |  | t <sub>rr</sub>     |     | 65   |      | ns   |
| Reverse Recovery Charge               | I <sub>S</sub> = 30A, dl/dt = 100A/μs      | Q <sub>rr</sub>     |     | 175  |      | nC   |

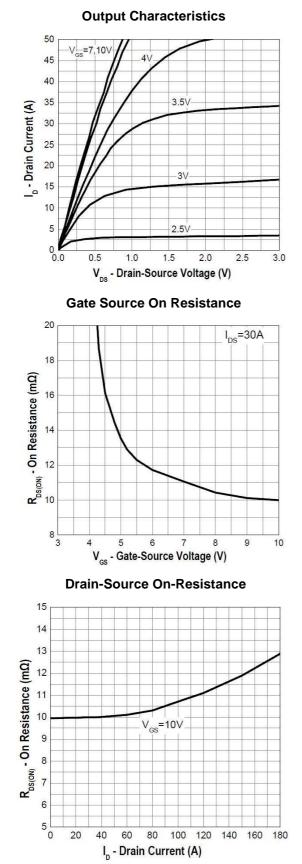
1. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

2.  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air

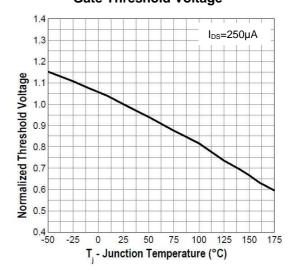
3. The maximum current is limited by package.



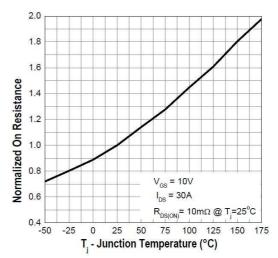
### **Electrical Characteristics Curves**



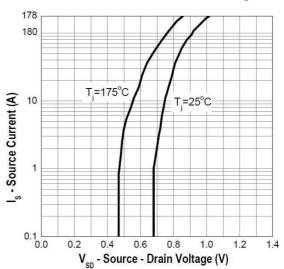
Gate Threshold Voltage



**Drain-Source On Resistance** 

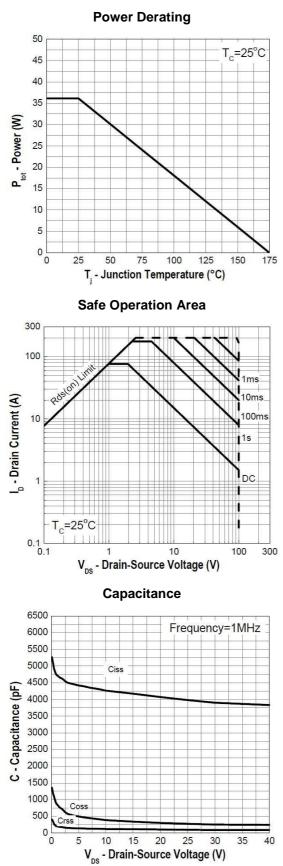


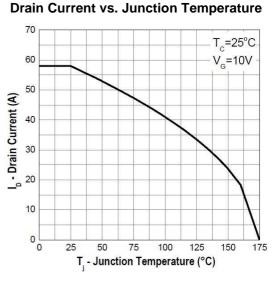
Source-Drain Diode Forward Voltage



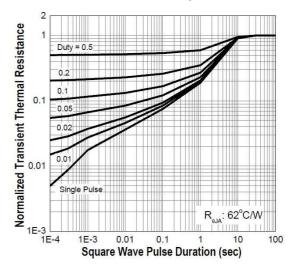


### **Electrical Characteristics Curves**

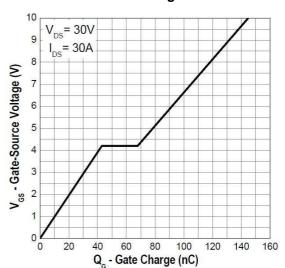




**Transient Thermal Impedance** 

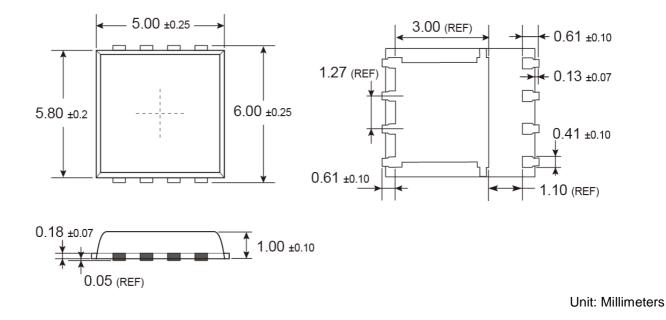


**Gate Charge** 





# **PDFN56 Mechanical Drawing**



## **Marking Diagram**



- Y = Year Code
- M = Month Code for Halogen Free Product
  (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
- L = Lot Code



### Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.